

Joint Technology Development by FORTH and Fraunhofer IZM

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Fraunhofer IZM collaborates with the **SMARTEC pilot line of the Foundation for Research and Technology (FORTH)** to develop, for the first time, 3D sequential integration for analog RF circuits and eventually offer this technology to the APECS pilot line ecosystem & beyond.

The SMARTEC pilot line is the result of a FTI EU project and focuses on III-V MMICs, RF MEMS and their (monolithic) integration

The department Wafer Level System Integration (WLSI) develops advanced packaging and system integration technologies and offers customer-specific solutions for microelectronic products in the overall scope of smart system integration.

Potential Impact

TELECOM

- Higher data rates
- Higher capacity
- Smaller antennas

RADAR

- SWaP & Multifunction systems
- Increase range & resolution
- Faster switching

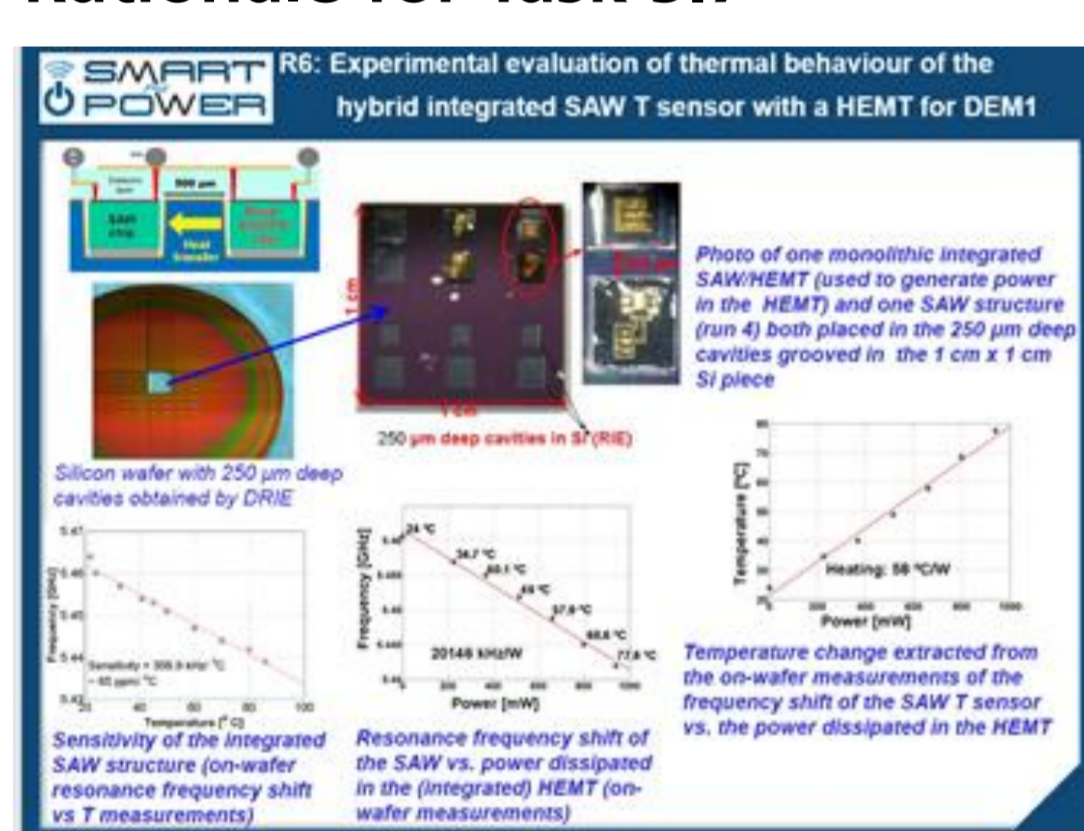
Alignment with APECS main objectives

- ✓ Next generation technologies for advanced packaging and heterogeneous integrated systems
- ✓ Advanced packaging concepts for communication in small form factors
- ✓ New process modules, to ensure quality, reliability and security of heterogeneously integrated chips and systems
- ✓ New design methodologies for heterogenous integrated systems in a single package with improved performances (power, higher frequency, less energy consumption)
- ✓ A sustainable pilot line, open to European stakeholders (especially for SMEs and start ups) from the entire value chain
- ✓ Skills development

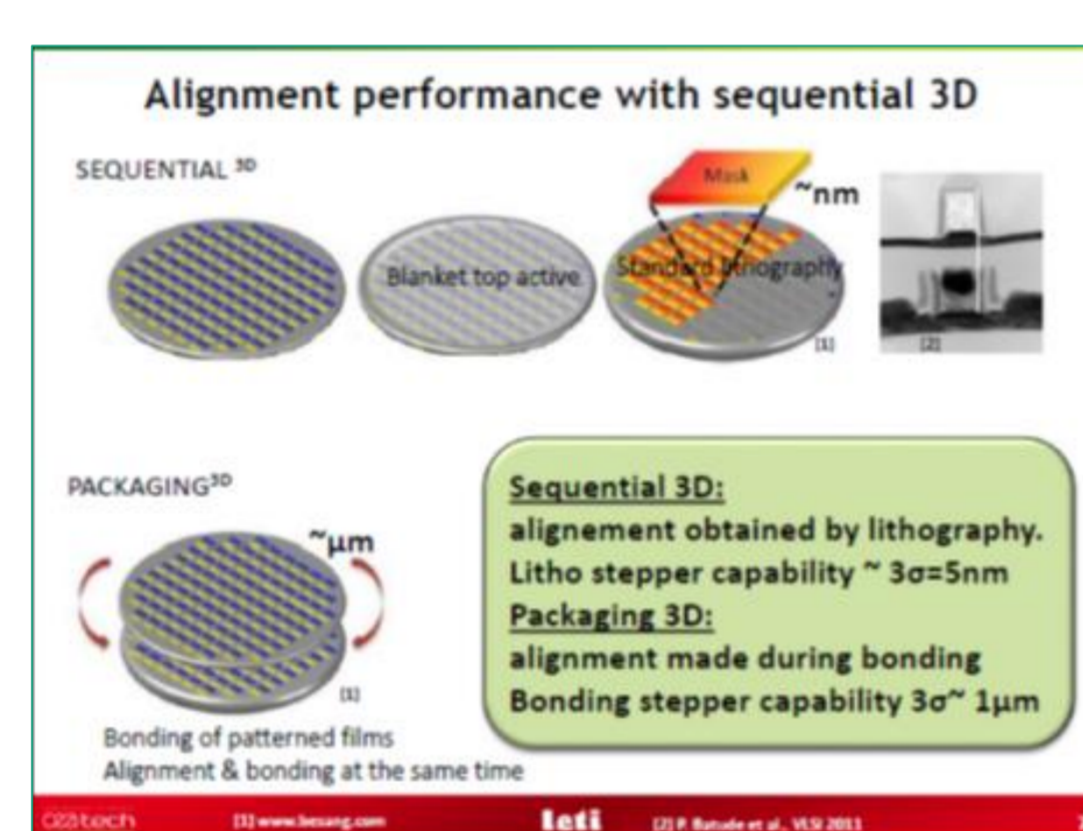
Next Steps (Q1 & Q2 2026)

1. Complete LA stage and initiate tests
2. Develop TSV technology
3. Fabricate HPA on GaN 1 with existing design
4. Complete 1st 3D stack with TSV interconnects
5. Test functionality

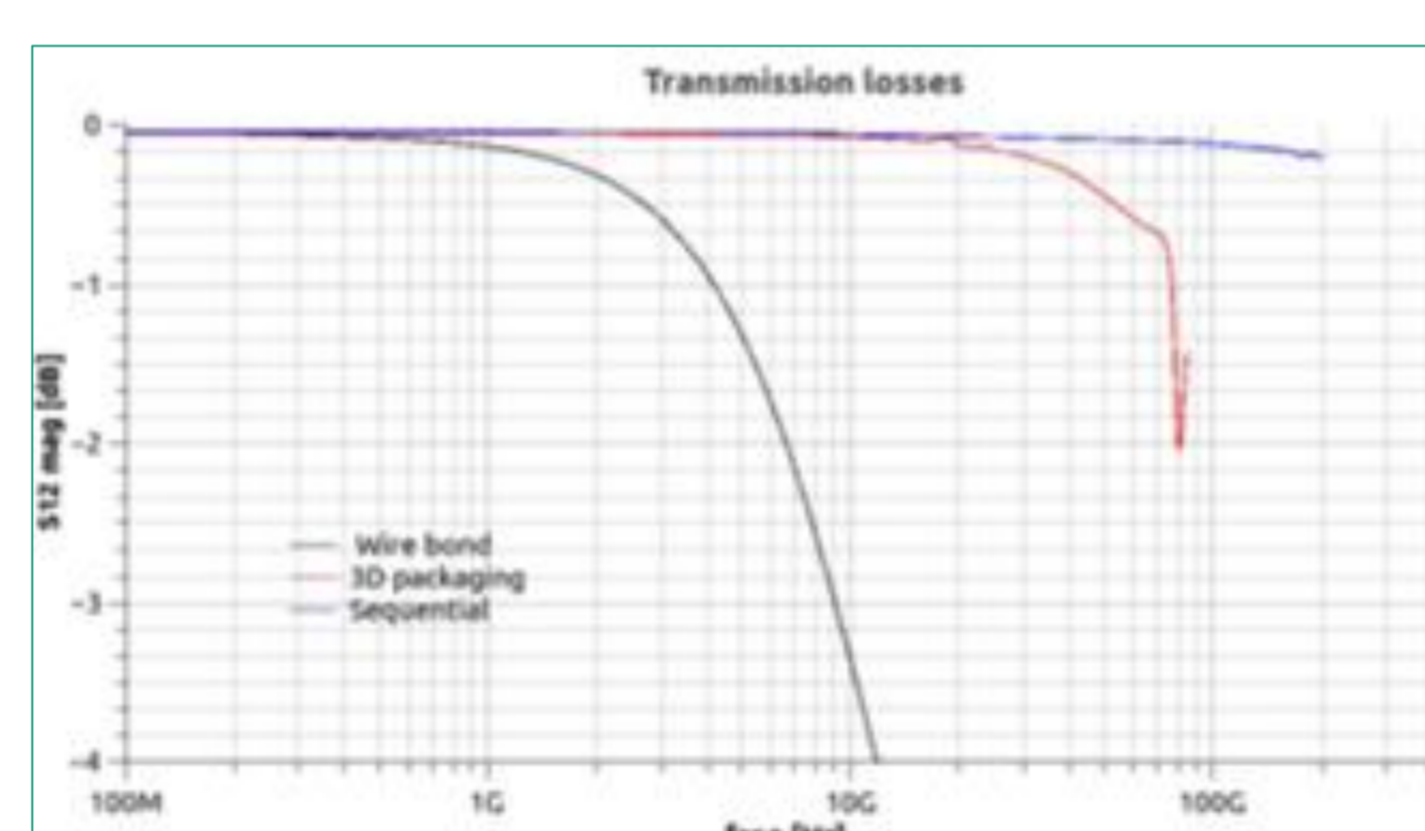
Rationale for Task 5.7



Proven past successful collaboration (FORTH & WLSI)



3DSI in analogue RF systems promises to dramatically reduce losses due to much shorter interconnects (ADS) & improve RF performance especially above 30GHz



Joint Technology Development

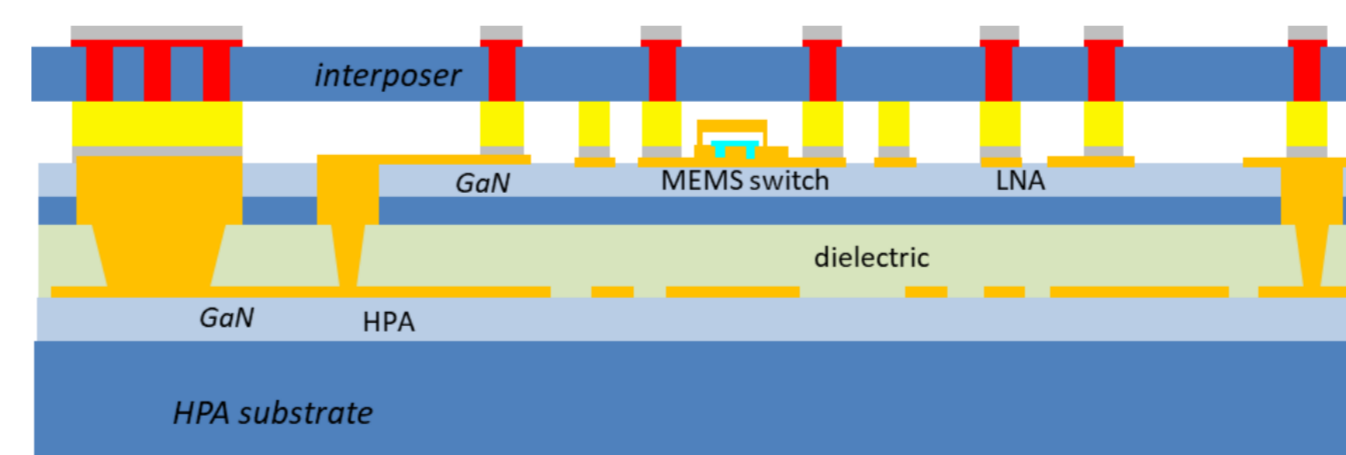


Main application: SiP RF front ends for radars and communications

3D Sequential Integration (3D SI) of GaN & RF MEMS based RF front end (RFFE) chips

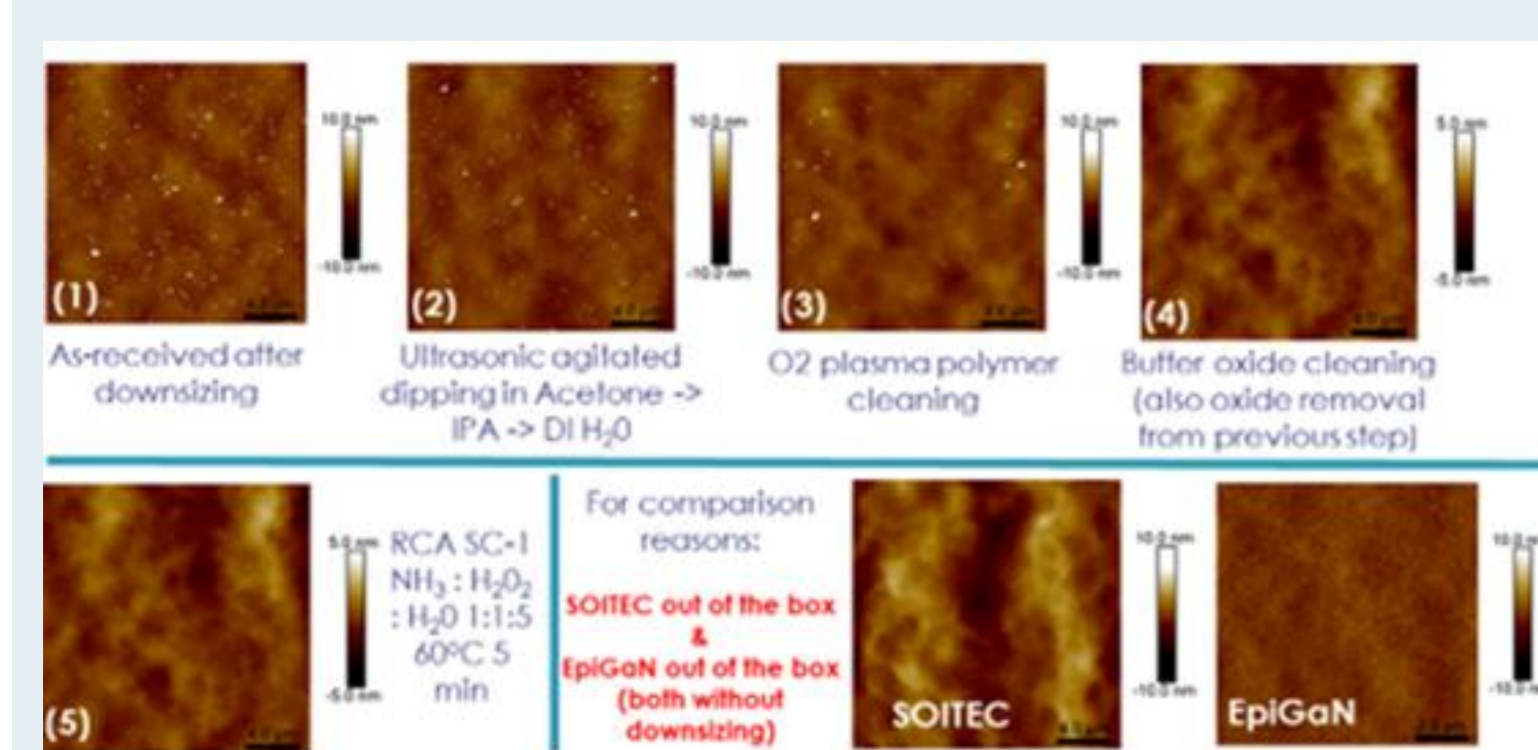
3DSI concept & Main challenges:

- Wafer-to-wafer stacking of GaN wafers (**voids, thermomechanical**)
- Si, SiC and Si GaN substrates (**HPA functionality & reliability**)
- Sequential processing of GaN wafers (**LNA ohmic contact/laser annealing**)
- TSV formation & filling (**voidfree TSV filling, low RF losses**)
- Hermetic Sealing of MEMS with silicon interposer (**device reliability**)

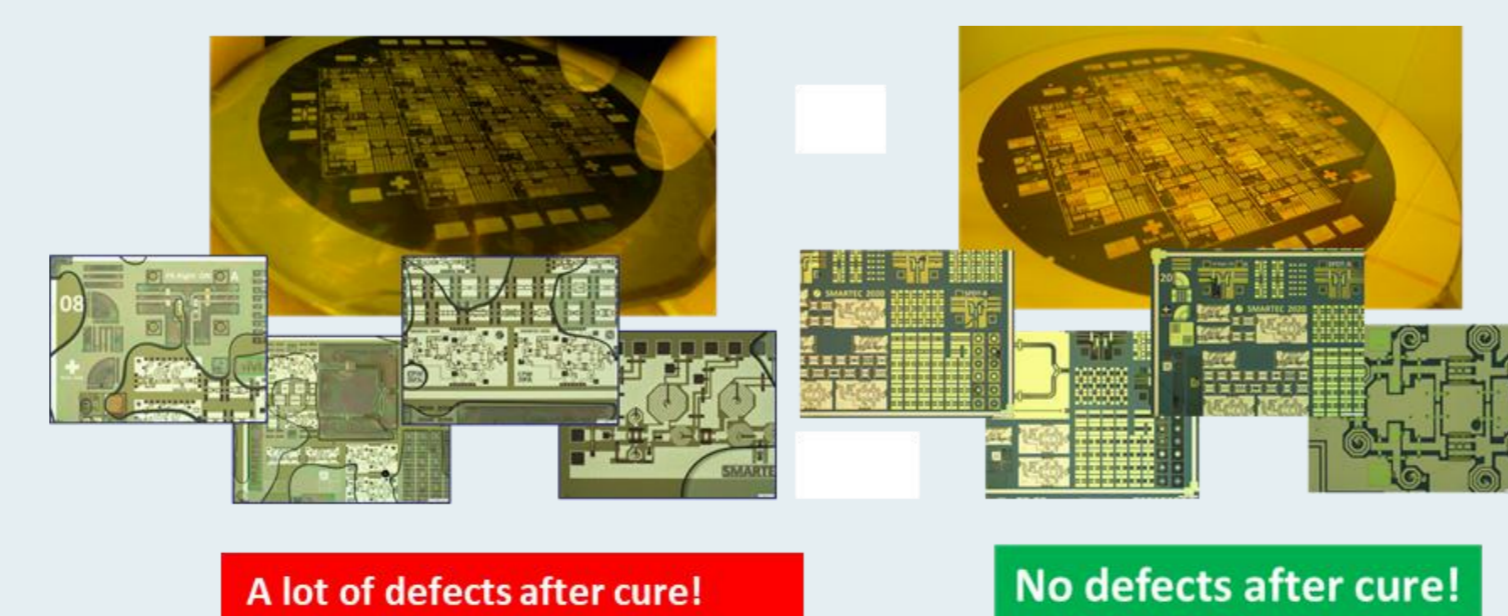


Main Results Y1

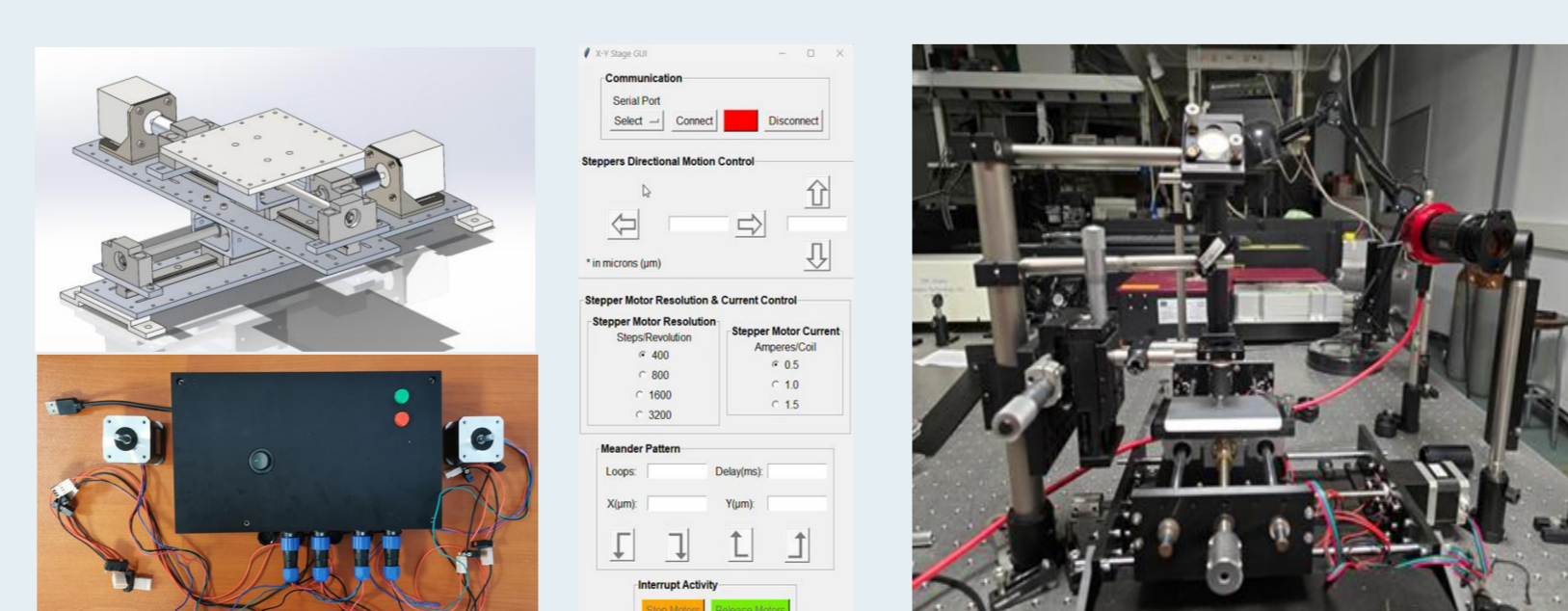
Wafer downsizing and post process cleaning



Suppression of voids In 3D stacking



LA stage in final steps of development



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Additional information

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Views and opinions expressed are however those of the author(s) only and do not necessarily reflect those of the European Union or the Chips Joint Undertaking. Neither the European Union nor the granting authority can be held responsible for them.

